

## Silicon NPN Power Transistors

2SD531

## DESCRIPTION

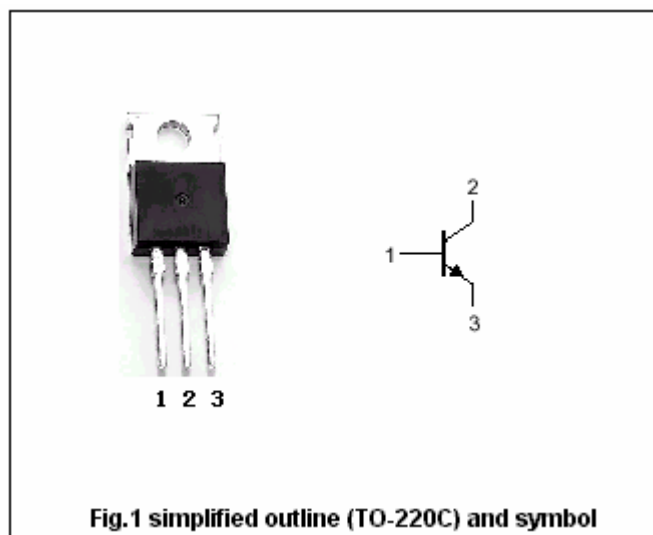
- With TO-220C package
- High current capability

## APPLICATIONS

- For audio frequency power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_c=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	100	V
$V_{CEO}$	Collector-emitter voltage	Open base	90	V
$V_{EBO}$	Emitter-base voltage	Open collector	8	V
$I_C$	Collector current		5	A
$P_C$	Collector power dissipation	$T_c=25$	43	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA; R <sub>BE</sub> =	90			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =5mA; I <sub>E</sub> =0	100			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =5mA; I <sub>C</sub> =0	8			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.4 A			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =2V	60			

固电半导体  
INCHANGE SEMICONDUCTOR

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PACKAGE OUTLINE

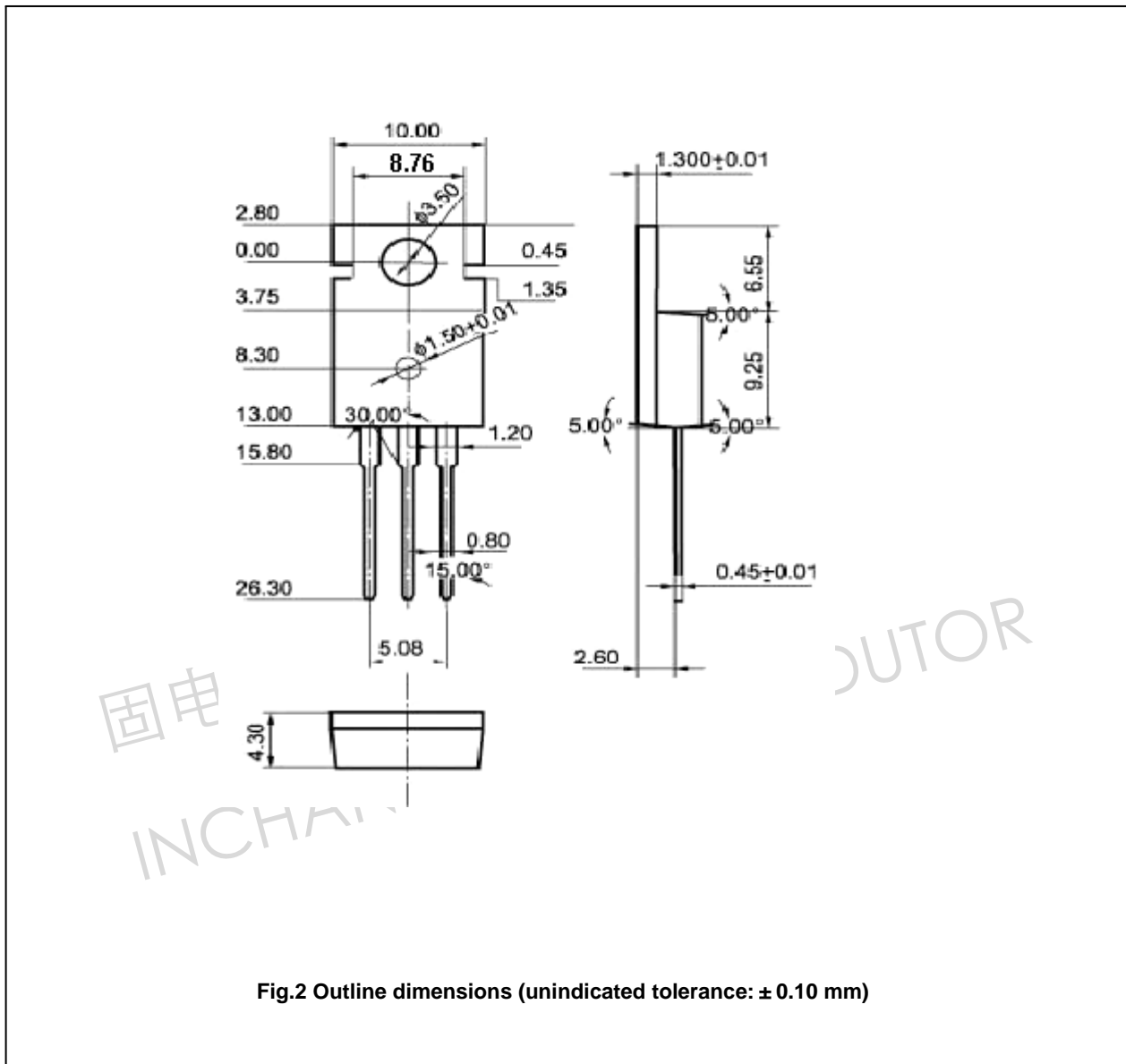


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)